

**WEST**[Generate Collection](#)[Print](#)**Search Results - Record(s) 1 through 6 of 6 returned.**☐ 1. Document ID: US 6383942 B1

L4: Entry 1 of 6

File: USPT

May 7, 2002

US-PAT-NO: 6383942

DOCUMENT-IDENTIFIER: US 6383942 B1

TITLE: Dry etching method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

[KVMC](#)☐ 2. Document ID: US 5963812 A

L4: Entry 2 of 6

File: USPT

Oct 5, 1999

US-PAT-NO: 5963812

DOCUMENT-IDENTIFIER: US 5963812 A

TITLE: Manufacturing method of a semiconductor apparatus having an electron donative surface in a side wall portion

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

[KVMC](#)☐ 3. Document ID: US 5580808 A

L4: Entry 3 of 6

File: USPT

Dec 3, 1996

US-PAT-NO: 5580808

DOCUMENT-IDENTIFIER: US 5580808 A

TITLE: Method of manufacturing a ROM device having contact holes treated with hydrogen atoms and energy beam

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

[KVMC](#)☐ 4. Document ID: US 5569614 A

L4: Entry 4 of 6

File: USPT

Oct 29, 1996

US-PAT-NO: 5569614

DOCUMENT-IDENTIFIER: US 5569614 A

TITLE: Method of forming metal pattern including a schottky diode

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

5. Document ID US 5527730 A

L4: Entry 5 of 6

File: USPT

Jun 18, 1996

US-PAT-NO: 5527730

DOCUMENT-IDENTIFIER: US 5527730 A

TITLE: Method of forming a capacitor having contact hole treated with hydrogen atoms and energy beam

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

6. Document ID: US 5393565 A

L4: Entry 6 of 6

File: USPT

Feb 28, 1995

US-PAT-NO: 5393565

DOCUMENT-IDENTIFIER: US 5393565 A

TITLE: Method for deposition of a refractory metal nitride and method for formation of a conductive film containing a refractory metal nitride

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

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L1 and (reactive adj gases)

6

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L9: Entry 1 of 27

File: USPT

Dec 31, 2002

US-PAT-NO: 6500742

DOCUMENT-IDENTIFIER: US 6500742 B1

TITLE: Construction of a film on a semiconductor wafer ✓

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KIMC

☐ 2. Document ID: US 6495458 B2

L9: Entry 2 of 27

File: USPT

Dec 17, 2002

US-PAT-NO: 6495458

DOCUMENT-IDENTIFIER: US 6495458 B2

TITLE: Method for producing low carbon/oxygen conductive layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KIMC

☐ 3. Document ID: US 6491978 B1

L9: Entry 3 of 27

File: USPT

Dec 10, 2002

US-PAT-NO: 6491978

DOCUMENT-IDENTIFIER: US 6491978 B1

TITLE: Deposition of CVD layers for copper metallization using novel metal organic chemical vapor deposition (MOCVD) precursors ✓

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KIMC

☐ 4. Document ID: US 6465345 B1

L9: Entry 4 of 27

File: USPT

Oct 15, 2002

US-PAT-NO: 6465345

DOCUMENT-IDENTIFIER: US 6465345 B1

TITLE: Prevention of inter-channel current leakage in  
semiconductors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMMC

☐ 5. Document ID: US 6451692 B1

L9: Entry 5 of 27

File: USPT

Sep 17, 2002

US-PAT-NO: 6451692

DOCUMENT-IDENTIFIER: US 6451692 B1

TITLE: Preheating of chemical vapor deposition precursors

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMMC

☐ 6. Document ID: US 6448187 B2

L9: Entry 6 of 27

File: USPT

Sep 10, 2002

US-PAT-NO: 6448187

DOCUMENT-IDENTIFIER: US 6448187 B2

TITLE: Method of improving moisture resistance of low dielectric  
constant films

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMMC

☐ 7. Document ID: US 6444542 B2

L9: Entry 7 of 27

File: USPT

Sep 3, 2002

US-PAT-NO: 6444542

DOCUMENT-IDENTIFIER: US 6444542 B2

TITLE: Integrated circuit and method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments
Draw Desc	Image								

KMMC

☐ 8. Document ID: US 6444036 B2

L9: Entry 8 of 27

File: USPT

Sep 3, 2002

US-PAT-NO: 6444036

DOCUMENT-IDENTIFIER: US 6444036 B2

TITLE: Construction of a film on a semiconductor wafer

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KIMC
Draw Desc	Image									

☐ 9. Document ID: US 6403414 B2

L9: Entry 9 of 27

File: USPT

Jun 11, 2002

US-PAT-NO: 6403414

DOCUMENT-IDENTIFIER: US 6403414 B2

TITLE: Method for producing low carbon/oxygen conductive layers

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KIMC
Draw Desc	Image									

☐ 10. Document ID: US 6351039 B1

L9: Entry 10 of 27

File: USPT

Feb 26, 2002

US-PAT-NO: 6351039

DOCUMENT-IDENTIFIER: US 6351039 B1

TITLE: Integrated circuit dielectric and method

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KIMC
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L7 and tungsten

27



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IBM Technical Disclosure Bulletins 

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side by side

*DB=USPT; PLUR=YES; OP=ADJ*L9 L7 and tungstenL8 L7 and 438/\$.classL7 L5 and silaneL6 L5 and (stacked near barrier)L5 (Barrier adj layer) and (adhesion adj layer) and (copper) and  
((reactive adj gases) or TDMAT or TDEAT or TiCl4)L4 L1 and (reactive adj gases)L3 L1 and (adhesion near layer)L2 L1 near7 adhesionL1 stacked near2 barrier**Hit Count Set Name**

result set

27 L90 L829 L70 L668 L56 L43 L30 L2220 L1

END OF SEARCH HISTORY

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L3: Entry 1 of 3

File: USPT

Sep 10, 2002

US-PAT-NO: 6447826

DOCUMENT-IDENTIFIER: US 6447826 B1

TITLE: Packaging for meat and foodstuff

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 2. Document ID: US 6284595 B1

L3: Entry 2 of 3

File: USPT

Sep 4, 2001

US-PAT-NO: 6284595

DOCUMENT-IDENTIFIER: US 6284595 B1

TITLE: Method for fabricating stacked capacitor having excellent anti-oxidation property

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	Claims	KWIC
Draw Desc	Image										

☐ 3. Document ID: US 6228701 B1

L3: Entry 3 of 3

File: USPT

May 8, 2001

US-PAT-NO: 6228701

DOCUMENT-IDENTIFIER: US 6228701 B1

TITLE: Apparatus and method for minimizing diffusion in stacked capacitors formed on silicon plugs

Full	Title	Citation	Front	Review	Classification	Date	Reference	Sequences	Attachments	KWIC
Draw Desc	Image									

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L1 and (adhesion near layer)	3

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